

P54/74FCT821A/B/C (P54/74PCT821A/B/C) P54/74FCT823A/B/C (P54/74PCT823A/B/C) P54/74FCT825A/B/C (P54/74PCT825A/B/C) BUS INTERFACE REGISTERS

FEATURES

- Function, Pinout, and Drive Compatible with the FCT, F Logic, and Am29821/23/25
- FCT-C speed at 6.0ns max. (Com'I)
FCT-B speed at 7.5ns max. (Com'I)
- CMOS V_{OH} Levels for Low Power Consumption — Typically 1/3 of FAST Bipolar Logic
- Edge-rate Control Circuitry for Significantly Improved Noise Characteristics
- ESD protection exceeds 2000V
- Inputs and Outputs Interface Directly with TTL, NMOS, and CMOS Devices
- Outputs Meet Levels Required for CMOS Static RAM Low Power Standby Mode
- 64 mA Sink Current (Com'I), 48 mA (Mil)
15 mA Source Current (Com'I), 12 mA (Mil)
- Buffered Common Clock Enable (\overline{EN}) and Asynchronous Clear Input (CLR)
- Clamp Diodes on all Inputs for Ringing Suppression
- Manufactured in 0.8 micron PACE Technology™

DESCRIPTION

The 'FCT820 series bus interface registers are designed to eliminate the extra packages required to buffer existing registers and provide extra data width for wider address/data paths or buses carrying parity. The 'FCT821 is a buffered, 10 bit wide version of the popular 'FCT374 function. The 'FCT823 is a 9-bit wide buffered register with Clock Enable (EN) and Clear (CLR)—ideal for parity bus interfacing in high-performance microprogrammed systems. The 'FCT825 is a 8-bit buffered register with all the 'FCT823 controls plus multiple enables (\overline{OE}_1 , \overline{OE}_2 , \overline{OE}_3) to allow multiuser control of the interface, e.g., \overline{CS} , DMA and RD/WR. They are ideal for use as an output port requiring high I_{OL}/I_{OH} .

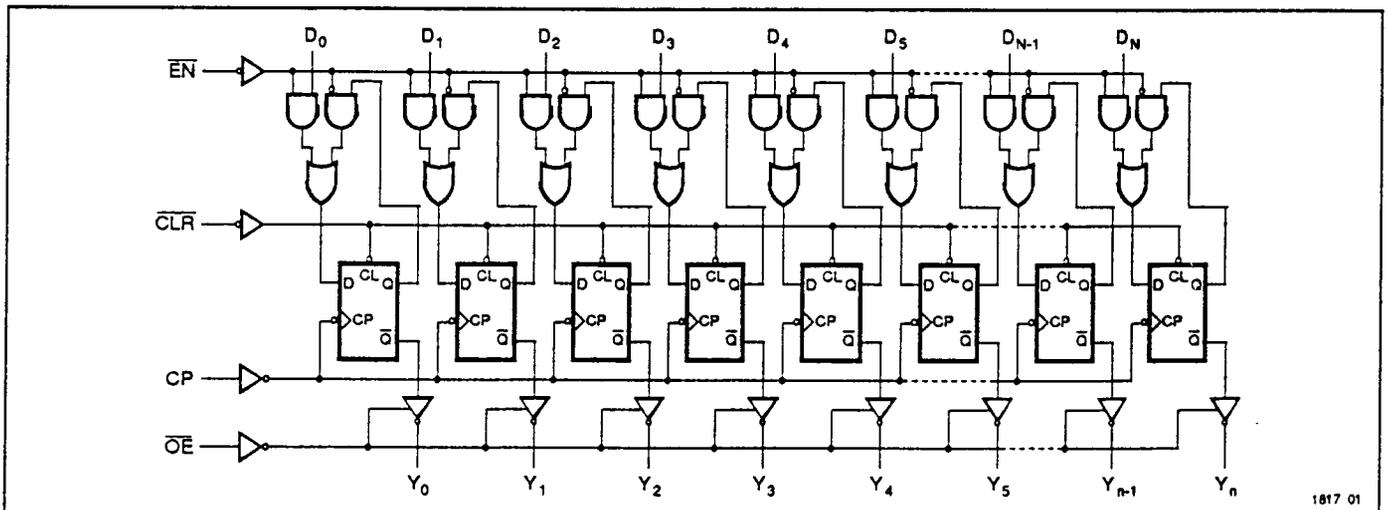
The 'FCT800 family of devices are designed for high-capacitance load drive capability, while providing low-

capacitance bus loading at both inputs and outputs. All inputs have clamp diodes and all outputs are designed for low-capacitance bus loading in the high impedance state.

The 'FCT820 interface family is manufactured using PACE Technology™ which is Performance Advanced CMOS Engineered to use 0.8 micron effective channel lengths giving 500 picoseconds loaded* internal gate delays. PACE Technology includes two-level metal and epitaxial substrates. In addition to very high performance and very high density, the technology features latch-up protection, single event upset protection, and is supported by a Class 1 environment volume production facility.

*For a fan-in/fan-out of 4, at 85°C junction temperature and 5.0V supply. For a fan-in/fan-out of 1, the internal gate delay is 200 picosecond at room temperature and 5.0V.

FUNCTIONAL BLOCK DIAGRAM



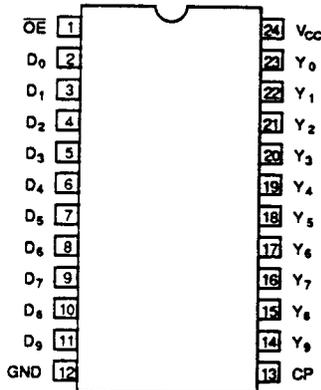
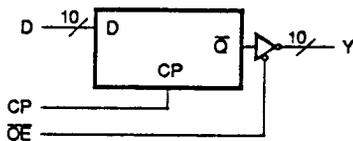
PRODUCT SELECTOR GUIDE

Non-inverting	Device		
	10-Bit	9-Bit	8-Bit
	'FCT821	'FCT823	'FCT825

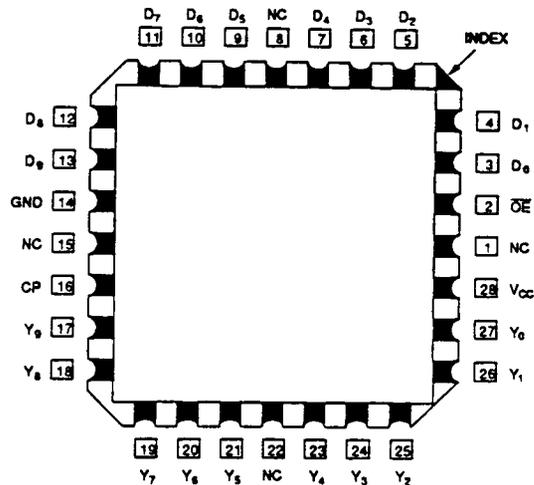
1817 Tbl 01

LOGIC SYMBOLS

'FCT821 (10-Bit Register)



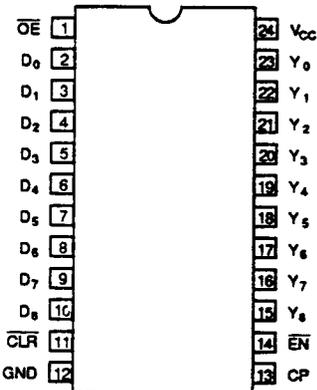
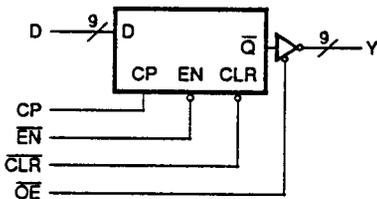
DIP (D4,P4) SOIC (S4)



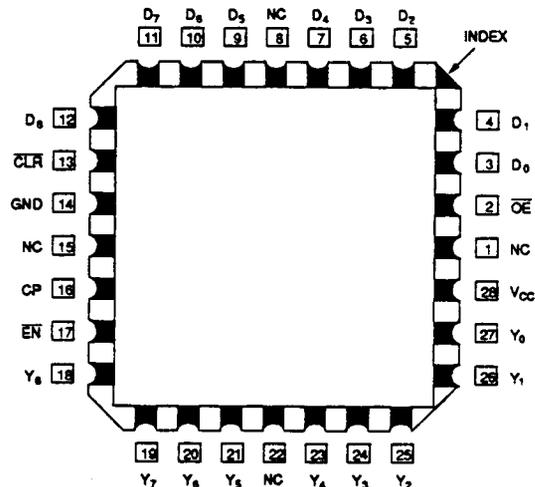
LCC (L5-1)

1817 02

'FCT823 (9-Bit Register)



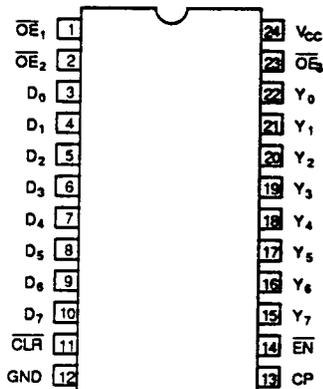
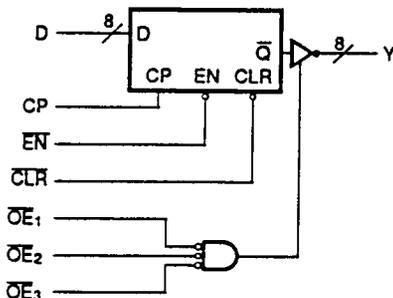
DIP (D4,P4) SOIC (S4)



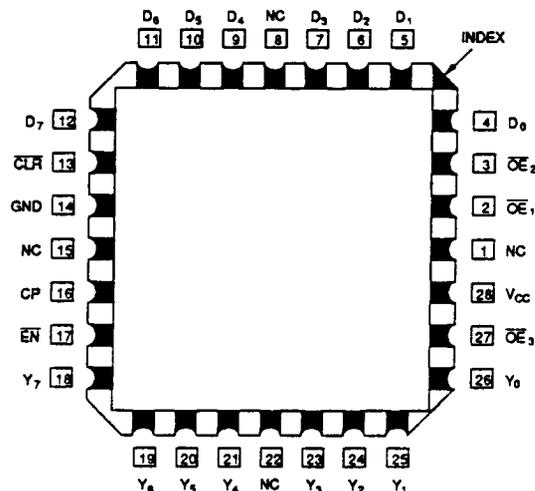
LCC (L5-1)

1817 03

'FCT825 (8-Bit Register)



DIP (D4,P4) SOIC (S4)



LCC (L5-1)

1817 04

ABSOLUTE MAXIMUM RATINGS^{1,2}

Symbol	Parameter	Value	Unit
T_{STG}	Storage Temperature	-65 to +150	°C
T_A	Ambient Temperature Under Bias	-65 to +135	°C
V_{CC}	V_{CC} Potential to Ground	-0.5 to +7.0	V
I_{IN}	Input Current	-30 to +5.0	mA

Notes:

1817 TH 02

- Operation beyond the limits set forth in the above table may impair the useful life of the device. Unless otherwise noted, these limits are over the operating free-air temperature range.

RECOMMENDED OPERATING CONDITIONS

Free Air Ambient Temperature	Min	Max
Military	-55°C	+125°C
Commercial	0°C	+70°C

1817 TH 04

Symbol	Parameter	Value	Unit
I_{OUTPUT}	Current Applied to Output	120	mA
V_{IN}	Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_{OUT}	Voltage Applied to Output	-0.5 to $V_{CC} + 0.5$	V

1817 TH 03

- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.

Supply Voltage (V_{CC})	Min	Max
Military	+4.5V	+5.5V
Commercial	+4.75V	+5.25V

1817 TH 05

DC ELECTRICAL CHARACTERISTICS (Over recommended operating conditions)

Symbol	Parameter	Min	Typ ¹	Max	Units	V_{CC}	Conditions	
V_{IH}	Input HIGH Voltage	2.0		$V_{CC} + 0.5$	V			
V_{IL}	Input LOW Voltage	-0.5		0.8	V			
V_H	Hysteresis		0.35		V		All inputs	
V_{CD}	Input Clamp Diode Voltage		-0.7	-1.2	V	MIN	$I_{IN} = -18\text{mA}$	
V_{OH}	Output HIGH Voltage	$V_{CC} = 3\text{V}$, $V_{IN} = 0.2\text{V}$, or $V_{CC} - 0.2\text{V}$	$V_{CC} - 0.2$	V_{CC}	V		$I_{OH} = -32\mu\text{A}$	
		Military/Commercial (CMOS)	$V_{CC} - 0.2$	V_{CC}	V	MIN	$I_{OH} = -300\mu\text{A}$	
		Military (TTL)	2.4	4.3	V	MIN	$I_{OH} = -12\text{mA}$	
		Commercial (TTL)	2.4	4.3	V	MIN	$I_{OH} = -15\text{mA}$	
V_{OL}	Output LOW Voltage	$V_{CC} = 3\text{V}$, $V_{IN} = 0.2\text{V}$, or $V_{CC} - 0.2\text{V}$		GND	0.2	V	$I_{OL} = 300\mu\text{A}$	
		Military/Commercial (CMOS)		GND	0.2	V	MIN	$I_{OL} = 300\mu\text{A}$
		Military (TTL)		0.3	0.5	V	MIN	$I_{OL} = 32\text{mA}$
		Commercial (TTL)		0.3	0.5	V	MIN	$I_{OL} = 48\text{mA}$
		Commercial (TTL)		0.3	0.5	V	MIN	$I_{OL} = 64\text{mA}$
I_{IH}	Input HIGH Current			5	μA	MAX	$V_{IN} = V_{CC}$	
I_{IL}	Input LOW Current			-5	μA	MAX	$V_{IN} = \text{GND}$	
I_{IH}^3	Input HIGH Current ³			5	μA	MAX	$V_{IN} = 2.7\text{V}$	
I_{IL}^3	Input LOW Current ³			-5	μA	MAX	$V_{IN} = 0.5\text{V}$	
I_{OZH}	Off State I_{OUT} HIGH-Level Output Current			10	μA	MAX	$V_{OUT} = V_{CC}$	
I_{OZL}	Off State I_{OUT} LOW-Level Output Current			-10	μA	MAX	$V_{OUT} = \text{GND}$	
I_{OZH}^3	Off State I_{OUT} HIGH-Level Output Current ³			10	μA	MAX	$V_{OUT} = 2.7\text{V}$	
I_{OZL}^3	Off State I_{OUT} LOW-Level Output Current ³			-10	μA	MAX	$V_{OUT} = 0.5\text{V}$	
I_{OS}	Output Short Circuit Current ²	-60	-120	-225	mA	MAX	$V_{OUT} = 0.0\text{V}$	
C_{IN}	Input Capacitance ³		5	10	pF	MAX	All inputs	
C_{OUT}	Output Capacitance ³		9	12	pF	MAX	All outputs	

Notes:

1817 TH 06

- Typical limits are at $V_{CC} = 5.0\text{V}$, $T_A = +25^\circ\text{C}$ ambient.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect

operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

- This parameter is guaranteed but not tested.

DC CHARACTERISTICS (Over recommended operating conditions unless otherwise specified.)

Symbol	Parameter	Typ ¹	Max	Units	Conditions
I_{CC}	Quiescent Power Supply Current (CMOS inputs)	0.003	0.5	mA	$V_{CC} = \text{MAX}$, $f_1 = 0$, Outputs Open, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs)	0.5	2.0	mA	$V_{CC} = \text{MAX}$, $V_{IN} = 3.4V^2$, $f_1 = 0$, Outputs Open
I_{CCD}	Dynamic Power Supply Current ³	0.15	0.25	mA/ mHz	$V_{CC} = \text{MAX}$, One Bit Toggling, 50% Duty Cycle, Outputs Open, $\overline{OE} = \overline{EN} = \text{GND}$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
I_C	Total Power Supply Current ⁵	1.7	4.0	mA	$V_{CC} = \text{MAX}$, $f_0 = 10\text{MHz}$, 50% Duty Cycle, Outputs Open, One Bit Toggling at $f_1 = 5\text{MHz}$, $\overline{OE} = \overline{EN} = \text{GND}$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		2.2	6.0	mA	$V_{CC} = \text{MAX}$, $f_0 = 10\text{MHz}$, 50% Duty Cycle, Outputs Open, One Bit Toggling at $f_1 = 5\text{MHz}$, $\overline{OE} = \overline{EN} = \text{GND}$, $V_{IN} = 3.4V$ or $V_{IN} = \text{GND}$
		4.0	7.8 ⁴	mA	$V_{CC} = \text{MAX}$, $f_0 = 10\text{MHz}$, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at $f_1 = 2.5\text{MHz}$, $\overline{OE} = \overline{EN} = \text{GND}$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		6.2	16.8 ⁴	mA	$V_{CC} = \text{MAX}$, $f_0 = 10\text{MHz}$, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at $f_1 = 2.5\text{MHz}$, $\overline{OE} = \overline{EN} = \text{GND}$, $V_{IN} = 3.4V$ or $V_{IN} = \text{GND}$

1817 TB 07

- Notes:**
- Typical values are at $V_{CC} = 5.0V$, $+25^\circ\text{C}$ ambient.
 - Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND.
 - This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
 - Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
 - $I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$
 $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_0/2 + f_1 N_1)$
 I_{CC} = Quiescent Current with CMOS input levels
 ΔI_{CC} = Power Supply Current for a TTL High Input ($V_{IN} = 3.4V$)
- D_H = Duty Cycle for TTL Inputs High
 N_T = Number of TTL Inputs at D_H
 I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
 f_0 = Clock Frequency for Register Devices (Zero for Non-Register Devices)
 f_1 = Input Frequency
 N_1 = Number of Inputs at f_1
 All currents are in milliamps and all frequencies are in megahertz.

AC CHARACTERISTICS

Sym.	Parameter	Test Conditions	'FCT821A/823A/825A				'FCT821B/823B/825B				'FCT821C/823C/825C				Units	Fig. No.
			MIL		COM'L		MIL		COM'L		MIL		COM'L			
			Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.		
t_{PLH} t_{PHL}	Propagation Delay Clock to Y_1 ($\overline{OE} = \text{LOW}$)	$C_L = 50\text{pF}$ $R_L = 500\Omega$	-	11.5	-	10.0	-	8.5	-	7.5	-	7.0	-	6.0	ns	1,5-
t_{PLH} t_{PHL}	Propagation Delay Clock to Y_1 ($\overline{OE} = \text{LOW}$)	$C_L = 300\text{pF}^2$ $R_L = 500\Omega$	-	20.0	-	20.0	-	16.0	-	15.0	-	13.5	-	12.5	ns	1,5
t_{PHL}	Propagation Delay Clear to Y_1	$C_L = 50\text{pF}$ $R_L = 500\Omega$	-	15.0	-	14.0	-	9.5	-	9.0	-	8.5	-	8.0	ns	1,5
t_{PZH} t_{PZL}	Output Enable Time \overline{OE} to $Y_1 \uparrow$	$C_L = 50\text{pF}$ $R_L = 500\Omega$	-	13.0	-	12.0	-	9.0	-	8.0	-	8.0	-	7.0	ns	1,7,8
t_{PZH} t_{PZL}	Output Enable Time \overline{OE} to $Y_1 \uparrow$	$C_L = 300\text{pF}^2$ $R_L = 500\Omega$	-	25.0	-	23.0	-	16.0	-	15.0	-	13.5	-	12.5	ns	1,7,8
t_{PHZ} t_{PHL}	Output Disable Time \overline{OE} to $Y_1 \uparrow$	$C_L = 5\text{pF}^2$ $R_L = 500\Omega$	-	8.0	-	7.0	-	7.0	-	6.5	-	6.2	-	6.2	ns	1,7,8
t_{PHZ} t_{PHL}	Output Disable Time \overline{OE} to $Y_1 \uparrow$	$C_L = 50\text{pF}$ $R_L = 500\Omega$	-	9.0	-	8.0	-	8.0	-	7.5	-	6.5	-	6.5	ns	1,7,8

1817 Td 06

AC OPERATING REQUIREMENTS

Sym.	Parameter	Test Conditions	'FCT821A/823A/825A				'FCT821B/823B/825B				'FCT821C/823C/825C				Units	Fig. No.
			MIL		COM'L		MIL		COM'L		MIL		COM'L			
			Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.	Min. ¹	Max.		
t_{su}	Data to CP Set-up Time	$C_L = 50\text{pF}$ $R_L = 500\Omega$	4.0	-	4.0	-	3.0	-	3.0	-	3.0	-	3.0	-	ns	4-
t_h	Data CP Hold Time		2.0	-	2.0	-	1.5	-	1.5	-	1.5	-	1.5	-	ns	4
t_{su}	Enable ($\overline{EN} \uparrow$) to CP Set-up Time		4.0	-	4.0	-	3.0	-	3.0	-	3.0	-	3.0	-	ns	9
t_h	Enable \overline{EN} Hold Time		2.0	-	2.0	-	0.0	-	0.0	-	0.0	-	0.0	-	ns	9-
t_{rec}	Clear Recovery ($\overline{CLR} \uparrow$) Time		7.0	-	6.0	-	6.0	-	6.0	-	6.0	-	6.0	-	ns	6
$t_w(H)$ $t_w(L)$	Clock Pulse Width HIGH or LOW		7.0	-	7.0	-	6.0	-	6.0	-	6.0	-	6.0	-	ns	5
$t_w(L)$	Clear ($\overline{CLR} = \text{LOW}$) Pulse Width		7.0	-	6.0	-	6.0	-	6.0	-	6.0	-	6.0	-	ns	5

1817 Td 09

Notes:

1. Minimum limits are guaranteed but not tested on Propagation Delays.
2. These parameters are guaranteed but not tested.

PIN DESCRIPTION

Name	I/O	Description
D ₁	I	The D flip-flop data inputs.
$\overline{\text{CLR}}$	I	For both inverting and non-inverting registers, when the clear input is LOW and $\overline{\text{OE}}$ is LOW, the Q ₁ outputs are LOW. When the clear input is HIGH, data can be entered into the register.
CP	O	Clock Pulse for the register; enters data into the register on the LOW-to-HIGH transition.
Y ₁ , $\overline{\text{Y}}_1$	O	The register three-state outputs.
$\overline{\text{EN}}$	I	Clock Enable. When the clock enable is LOW, data on the D ₁ input is transferred to the Q ₁ output on the LOW-to HIGH clock transition. When the clock enable is HIGH, the Q ₁ outputs do not change state, regardless of the data or clock input transitions.
$\overline{\text{OE}}$	I	Output Control. When the $\overline{\text{OE}}$ input is HIGH, the Y ₁ outputs are in the high impedance state. When the $\overline{\text{OE}}$ input is LOW, the TRUE register data is present at the Y ₁ outputs.

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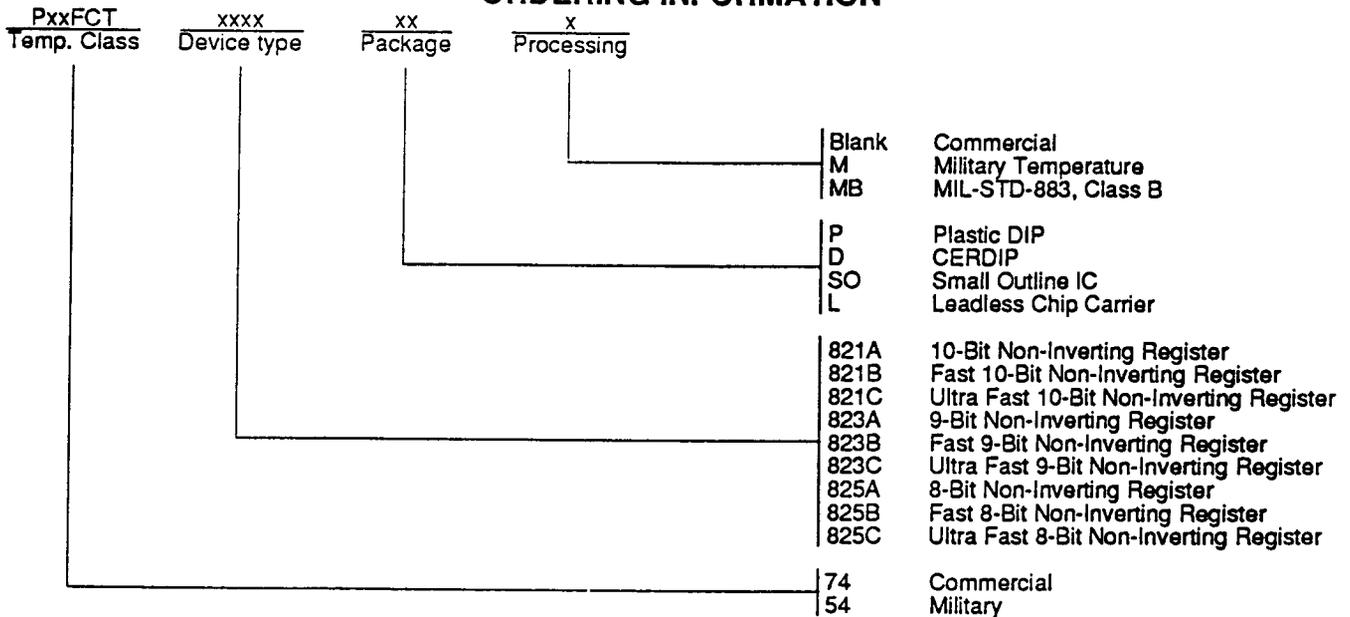
FUNCTION TABLES

Inputs					Internal Outputs		Function
OE	CLR	$\overline{\text{EN}}$	D ₁	CP	Q ₁	Y ₁	
H	H	L	L	\lrcorner	L	Z	High Z
H	H	L	H	\lrcorner	H	Z	
H	L	X	X	X	L	Z	Clear
L	L	X	X	X	L	L	
H	H	H	X	X	NC	Z	Hold
L	H	H	X	X	NC	NC	
H	H	L	L	\lrcorner	L	Z	Load
H	H	L	H	\lrcorner	H	Z	
L	H	L	L	\lrcorner	L	L	
L	H	L	H	\lrcorner	H	H	

1817 Tbl 11

H = HIGH, L = LOW, X = Don't Care, NC = No Change, \lrcorner = LOW-to-HIGH Transition, Z = HIGH Impedance

ORDERING INFORMATION



1817 05

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